

## MBRD650CT/MBRD660CT SCHOTTKY RECTIFIER

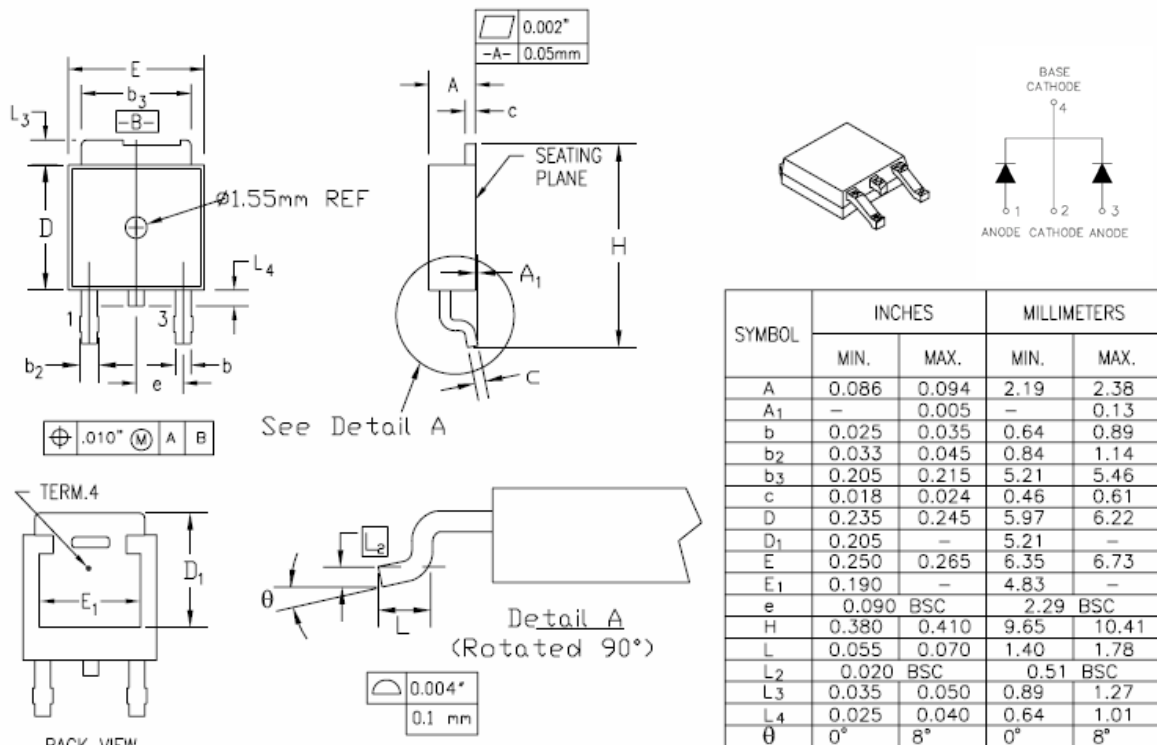
### Applications:

- Switching power supply
- Converters
- Free-Wheeling diodes
- Reverse battery protection

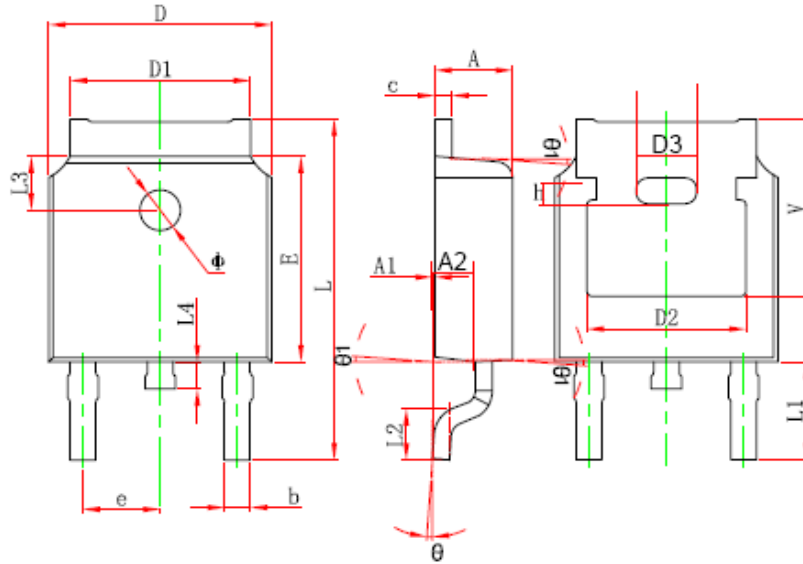
### Features:

- 150 °C T<sub>J</sub> operation
- Center tap configuration
- Low forward voltage drop
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability
- This is a Pb – Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

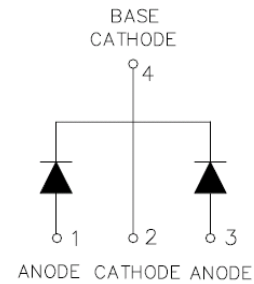
### Mechanical Dimensions: In Inches / mm



### OPTION 1(MX)



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	2.200	2.380	0.087	0.094
A1	0.000	0.100	0.000	0.004
b	0.710	0.810	0.028	0.032
c	0.460	0.560	0.018	0.022
D	6.500	6.700	0.256	0.264
D1	5.130	5.460	0.202	0.215
D2	4.830 REF.		0.190 REF.	
E	6.000	6.200	0.236	0.244
e	2.186	2.386	0.086	0.094
L	9.800	10.400	0.386	0.409
L1	2.900 REF.		0.114 REF.	
L2	1.400	1.700	0.055	0.067
L3	1.600 REF.		0.063 REF.	
L4	0.600	1.000	0.024	0.039
Φ	1.100	1.300	0.043	0.051
θ	0°	8°	0°	8°
A2	0.910	1.110	0.036	0.044
V	5.350 REF.		0.211 REF.	
D3	1.778 REF.		0.070 REF.	
h	0.762 REF.		0.030 REF.	
θ1	7°		7°	



**OPTION 2(CJ)**

**DPAK**

**Marking Diagram:**



Where XXXXX is YYWWL

MBR = Device Type  
D = Package type  
6 = Forward Current (6A)  
50 = Reverse Voltage (50V)  
CT = Configuration  
SSG = SSG  
YY = Year  
WW = Week  
L = Lot Number

**Cautions:** Molding resin  
Epoxy resin UL:94V-0

**Ordering Information:**

Device	Package	Shipping
MBRD650CT	DPAK (Pb-Free)	2500pcs / reel

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification.

**Maximum Ratings:**

Characteristics	Symbol	Condition	Max.		Units
			50	60	
Peak Inverse Voltage	$V_{RWM}$	-	50	60	V
Max. Average Forward	$I_{F(AV)}$	50% duty cycle @ $T_C=125^\circ\text{C}$ , rectangular wave form	6		A
Max. Peak One Cycle Non-Repetitive Surge Current (per leg)	$I_{FSM}$	8.3 ms, half Sine pulse	75		A

**Electrical Characteristics:**

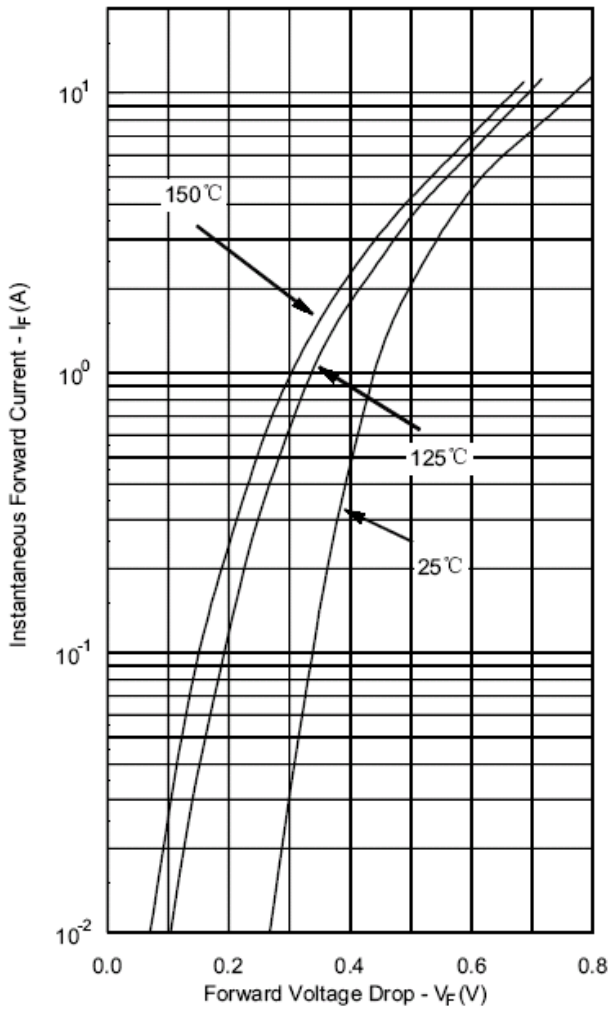
Characteristics	Symbol	Condition	Max.	Units
Max. Forward Voltage Drop	$V_{F1}$	@ 3A, Pulse, $T_J = 25\text{ }^\circ\text{C}$	0.70	V
		@ 6A, Pulse, $T_J = 25\text{ }^\circ\text{C}$	0.90	
	$V_{F1}$	@ 3A, Pulse, $T_J = 125\text{ }^\circ\text{C}$	0.65	V
		@ 6A, Pulse, $T_J = 125\text{ }^\circ\text{C}$	0.85	
Max. Reverse Current at DC condition	$I_{R1}$	@ $V_R = \text{rated } V_R$ $T_J = 25\text{ }^\circ\text{C}$	0.1	mA
Max. Reverse Current	$I_{R2}$	@ $V_R = \text{rated } V_R$ $T_J = 125\text{ }^\circ\text{C}$	15	mA
Max. Voltage Rate of Change	dv/dt	-	10,000	V/ $\mu\text{s}$

\* Pulse Width < 300 $\mu\text{s}$ , Duty Cycle <2%

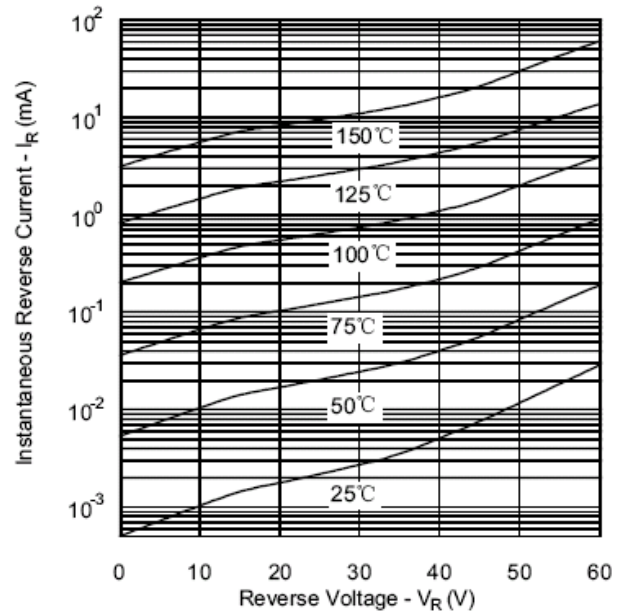
**Thermal-Mechanical Specifications:**

Characteristics	Symbol	Condition	Specification	Units
Junction Temperature Range	$T_J$	-	-65 to +150	$^\circ\text{C}$
Storage Temperature Range	$T_{\text{stg}}$	-	-65 to +175	$^\circ\text{C}$
Maximum Thermal Resistance Junction to Case	$R_{\theta\text{JC}}$	DC operation	6.0	$^\circ\text{C/W}$
Approximate Weight	wt	-	0.39	g
Case Style	DPAK			

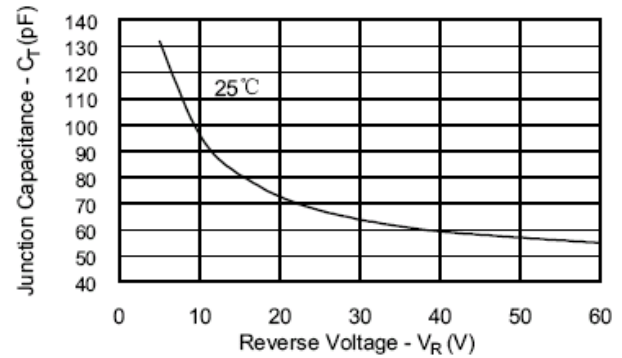
**Typical Forward Characteristics**



**Typical Reverse Characteristics**



**Typical Junction Capacitance**



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